

Title (en)

REFLECTIVE MASK BLANK FOR EUV LITHOGRAPHY AND METHOD FOR PRODUCING SAME

Title (de)

REFLEKTIERENDER MASKENROHLING FÜR DIE EUV-LITHOGRAPHIE UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

ÉBAUCHE DE MASQUE RÉFLÉCHISSANT POUR LITHOGRAPHIE EUV ET PROCÉDÉ DE FABRICATION DE LADITE ÉBAUCHE

Publication

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Application

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Priority

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Abstract (en)

A reflective-type mask blank for EUV lithography for reducing the EUV ray reflectance at the absorbing layer and a method for producing the mask blank are presented. A reflective-type mask blank for EUV lithography comprising a substrate and a reflective layer for reflecting EUV light and an absorbing layer for absorbing EUV light, which are formed on the substrate in this order, the reflective-type mask blank for EUV lithography being characterized in that the absorbing layer is a Cr layer of low EUV ray reflectance deposited by an ion beam sputtering method.

IPC 8 full level

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